

این دیتاشیت توسط توکل الکترونیک تهیه و ارائه شده است.
جهت مشاهده قیمت، موجودی و ثبت سفارش این قطعه به وبسایت توکل الکترونیک مراجعه فرمایید.



مشاهده قیمت و خرید

برای خرید و مشاهده سایر محصولات کلیک کنید

NEC
ELECTRON DEVICE

N-CHANNEL MOS FIELD EFFECT POWER TRANSISTORS

2SK1060, 2SK1060-Z

DESCRIPTION The 2SK1060, 2SK1060-Z are N-Channel MOS Field Effect Power Transistor designed for solenoid, motor and lamp driver.

- FEATURES**
- 4 V Gate Drive — Logic level —
 - Low $R_{DS(on)}$
 - No Second Breakdown
 - Designed for Hybrid Integrated Circuits

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures

Storage Temperature -55 to $+150$ °CJunction Temperature 150 °C Maximum

Maximum Power Dissipations

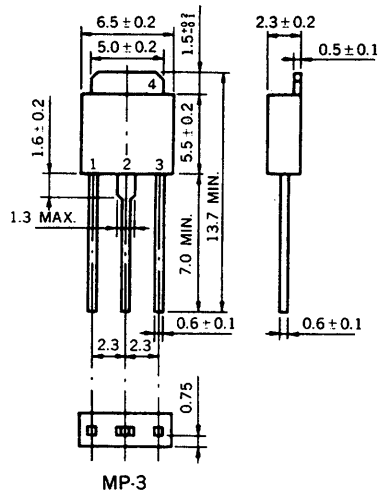
Total Power Dissipation* 2.0 W

Total Power Dissipation ($T_c^{**} = 25$ °C) . . 20 WMaximum Voltages and Currents ($T_a = 25$ °C) V_{DSS} Drain to Source Voltage 100 V V_{GSS} Gate to Source Voltage ± 20 V $I_{D(DC)}$ Drain Current (DC) ± 5 A $I_{D(pulse)}$ Drain Current (pulse)*** ± 20 A* Mounted on ceramic substrate of $7.5\text{ cm}^2 \times 0.7\text{ mm}$ ** $T_c = 25$ °C*** $PW \leq 10\text{ }\mu\text{s}$, Duty Cycle $\leq 1\%$ ELECTRICAL CHARACTERISTICS ($T_a = 25$ °C)

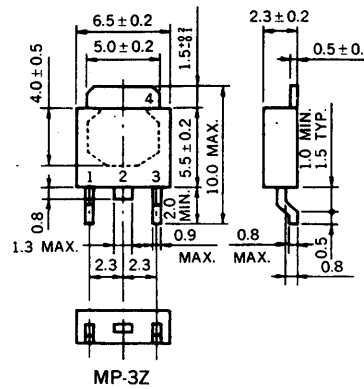
SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
$R_{DS(on)}$	Drain to Source On-State Resistance		0.18	0.27	Ω	$V_{GS} = 10\text{ V}$, $I_D = 3\text{ A}$
$R_{DS(on)}$	Drain to Source On-State Resistance		0.22	0.38	Ω	$V_{GS} = 4\text{ V}$, $I_D = 3\text{ A}$
$V_{GS(off)}$	Gate to Source Cutoff Voltage	1.0		2.5	V	$V_{DS} = 10\text{ V}$, $I_D = 1\text{ mA}$
$ y_{fs} $	Forward Transfer Admittance	4.0			S	$V_{DS} = 10\text{ V}$, $I_D = 3\text{ A}$
I_{DSS}	Drain Leakage Current			10	μA	$V_{DS} = 100\text{ V}$, $V_{GS} = 0$
I_{GSS}	Gate to Source Leakage Current			± 100	nA	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0$
C_{iss}	Input Capacitance		900		pF	$V_{DS} = 10\text{ V}$
C_{oss}	Output Capacitance		250		pF	$V_{GS} = 0$
C_{rss}	Reverse Transfer Capacitance		50		pF	$f = 1\text{ MHz}$
$t_{d(on)}$	Turn-On Delay Time		10		ns	$I_D = 3\text{ A}$, $V_{DD} = 50\text{ V}$ $R_L = 17\text{ }\Omega$ $R_{in} = 10\text{ }\Omega$
t_r	Rise Time		40		ns	
$t_{d(off)}$	Turn-Off Delay Time		110		ns	
t_f	Fall Time		30		ns	

PACKAGE DIMENSIONS (Unit : mm)

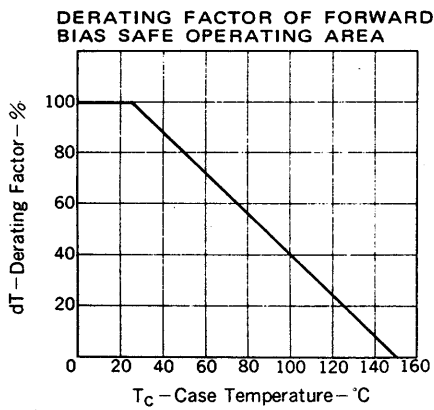
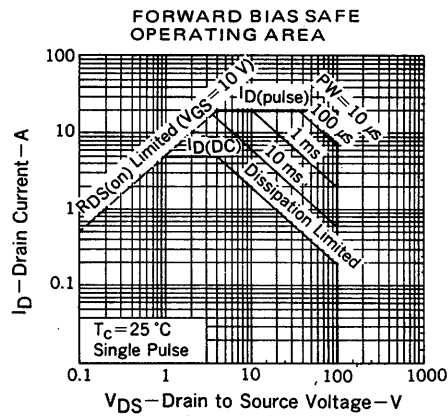
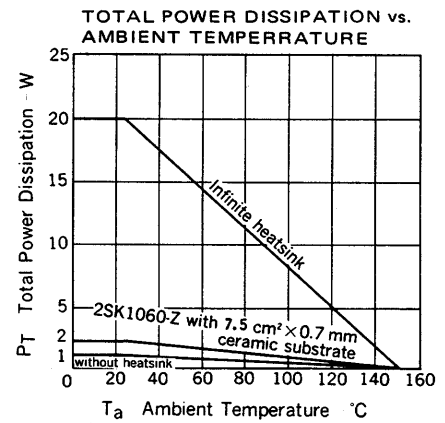
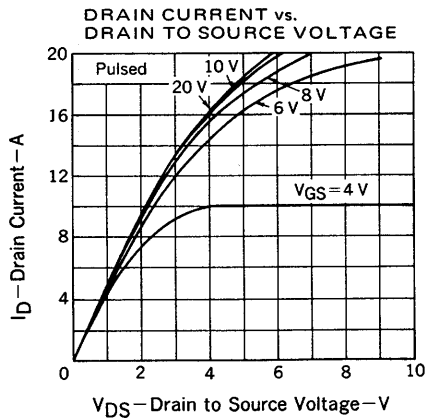
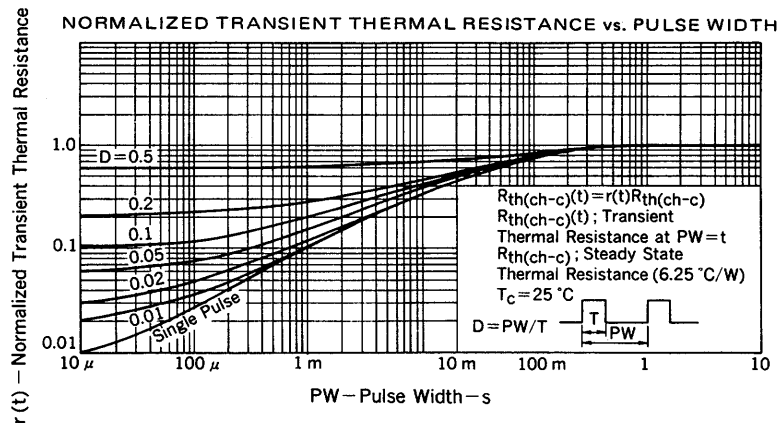
2SK1060

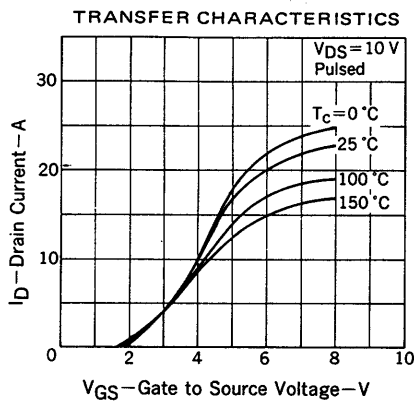
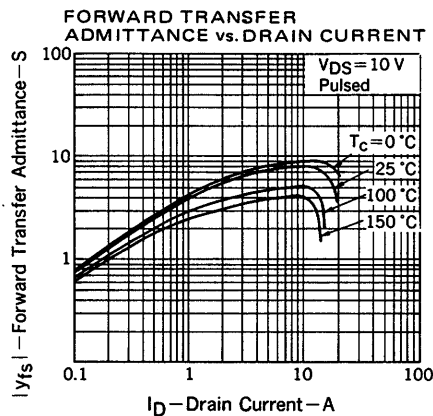
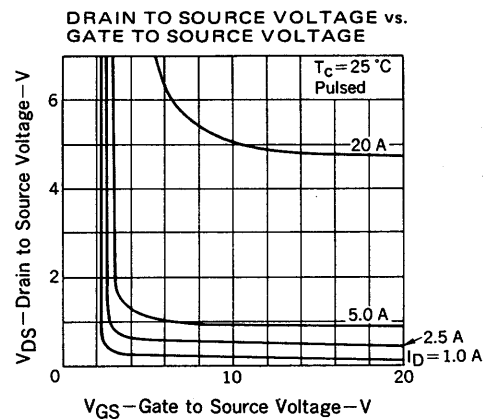
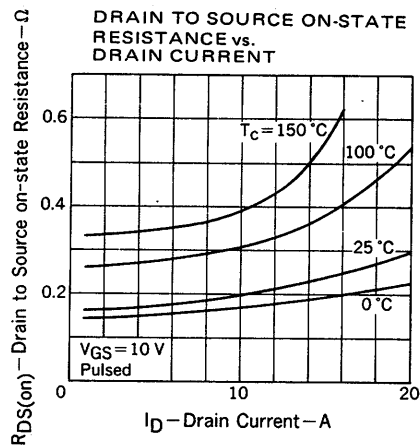
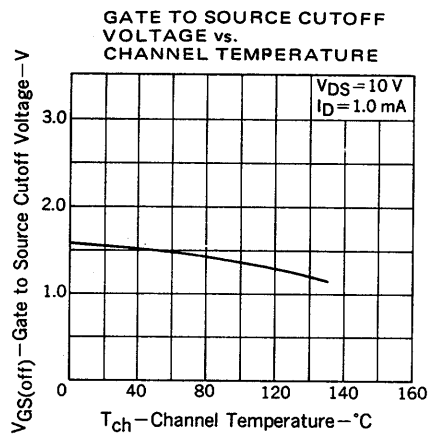
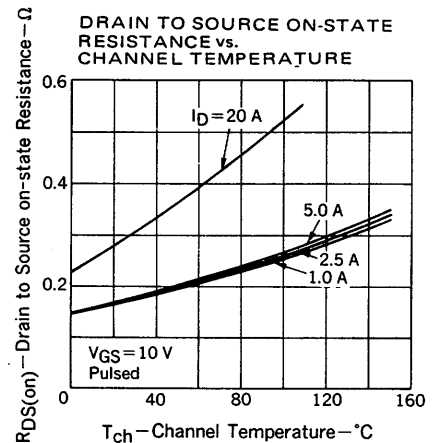
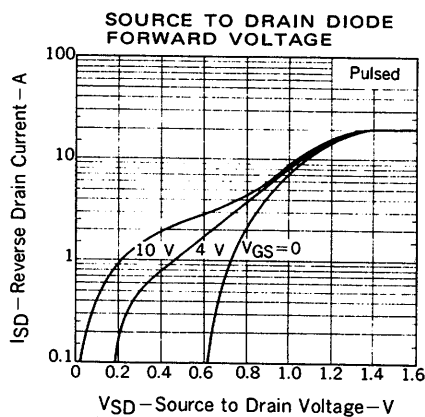
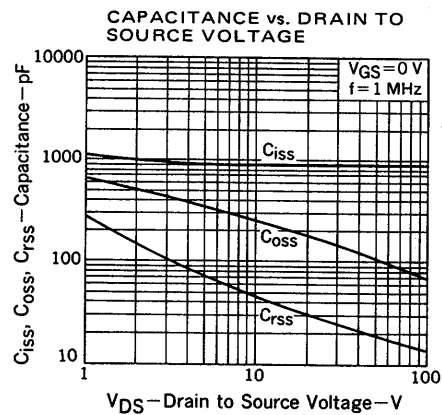
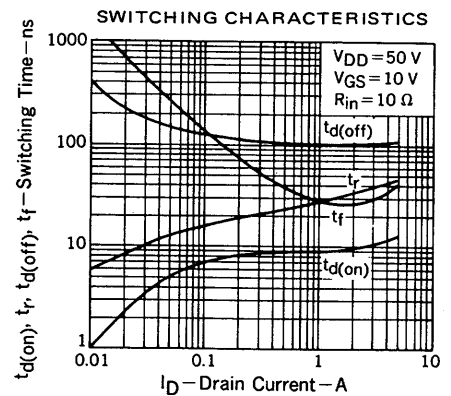


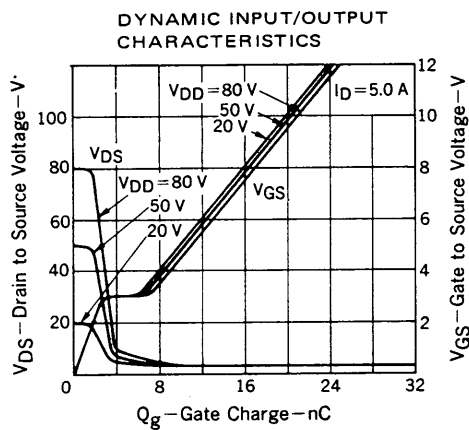
2SK1060-Z



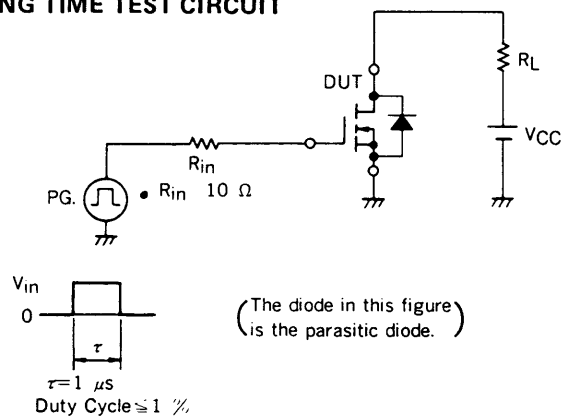
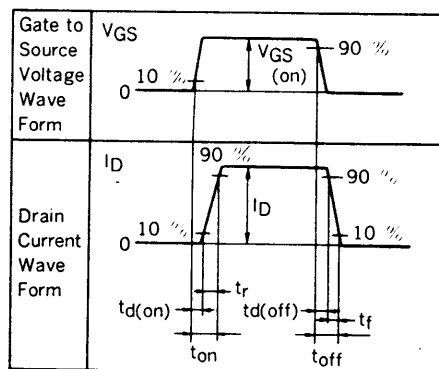
TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)







SWITCHING TIME TEST CIRCUIT



GATE CHARGE TEST CIRCUIT

